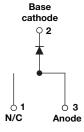
Vishay Semiconductors

## HEXFRED<sup>®</sup> Ultrafast Soft Recovery Diode, 25 A



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PRIMARY CHARACTERISTICS								
I <sub>F(AV)</sub>	25 A							
V <sub>R</sub>	600 V							
V <sub>F</sub> at I <sub>F</sub>	1.3 V							
t <sub>rr</sub> (typ.)	23 ns							
T <sub>J</sub> max.	150 °C							
Package	D <sup>2</sup> PAK (TO-263AB)							
Circuit configuration	Single							

## FEATURES

- Ultrafast and ultrasoft recovery
- Very low I<sub>RRM</sub> and Q<sub>rr</sub>
- Specified at operating conditions
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C



HALOGEN

FREE

- AEC-Q101 qualified, meets JESD 201 class 1A
   whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

### BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

### DESCRIPTION

VS-HFA25TB60S is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 25 A continuous current, the VS-HFA25TB60S is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (IRBM) and does not exhibit any tendency to "snap-off" during the t<sub>b</sub> portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA25TB60S is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Cathode to anode voltage	V <sub>R</sub>		600	V					
Maximum continuous forward current	IF	T <sub>C</sub> = 100 °C	25						
Single pulse forward current	I <sub>FSM</sub>		225	А					
Maximum repetitive forward current	I <sub>FRM</sub>		100						
Maximum power dissipation	PD	T <sub>C</sub> = 25 °C	125	W					
Maximum power dissipation		T <sub>C</sub> = 100 °C	50	vv					
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +150	°C					

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Document Number: 94675

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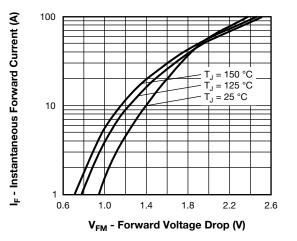
<b>ELECTRICAL SPECIFICATIONS</b> ( $T_J = 25 \ ^{\circ}C$ unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS		
Cathode to anode breakdown voltage	V <sub>BR</sub>	I <sub>R</sub> = 100 μA	600	-	-				
Maximum forward voltage		I <sub>F</sub> = 25 A		-	1.3	1.7	V		
	V <sub>FM</sub>	I <sub>F</sub> = 50 A	See fig. 1	-	1.5	2.0			
		I <sub>F</sub> = 25 A, T <sub>J</sub> = 125 °C		-	1.3	1.7			
Maximum reverse		$V_{R} = V_{R}$ rated	$V_{\rm R} = V_{\rm R}$ rated		1.5	20			
leakage current	IRM	$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	See fig. 2	-	600	2000	μA		
Junction capacitance	CT	V <sub>R</sub> = 200 V See fig. 3		-	55	100	pF		
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from p	ackage body	-	8.0	-	nH		

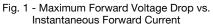
<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
Reverse recovery time See fig. 5	t <sub>rr</sub>	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200$	A/μs, V <sub>R</sub> = 30 V	-	23	-	ns		
	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	50	-			
	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C	I <sub>F</sub> = 25 A dI <sub>F</sub> /dt = 200 A/µs V <sub>R</sub> = 200 V	-	105	-			
Peak recovery current	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C		-	4.5	-	А		
See fig. 6	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C		-	8.0	-	A		
Reverse recovery charge	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	112	-	nC		
See fig. 7	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	420	-			
Peak rate of fall recovery current during t <sub>b</sub> See fig. 8	dl <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	250	-			
	dl <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	160	-	A/µs		

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C			
Thermal resistance, junction to case	R <sub>thJC</sub>		-	-	1.0	K/W			
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Typical socket mount	-	-	80	N/ ¥¥			
Weight			-	2.0	-	g			
weigin			-	0.07	-	oz.			
Marking device		Case style D <sup>2</sup> PAK (TO-263AB)		HFA25	TB60SH				



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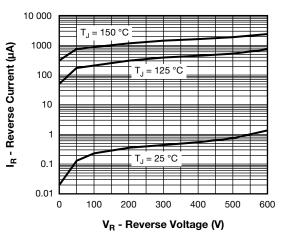


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

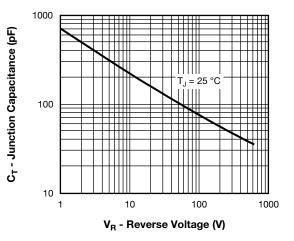


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

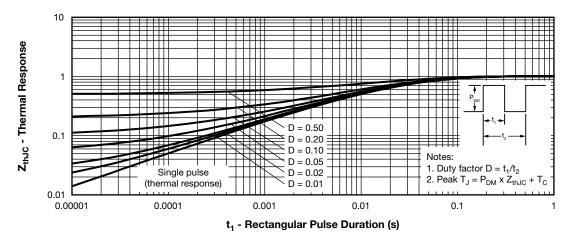


Fig. 4 - Maximum Thermal Impedance  $Z_{\text{thJC}}$  Characteristics



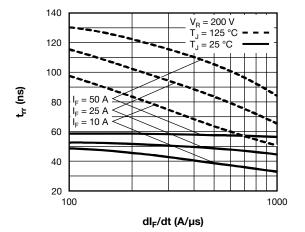


Fig. 5 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

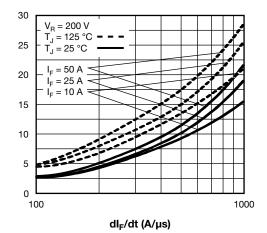
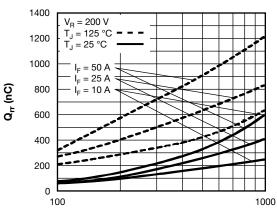


Fig. 6 - Typical Recovery Current vs. dl<sub>F</sub>/dt







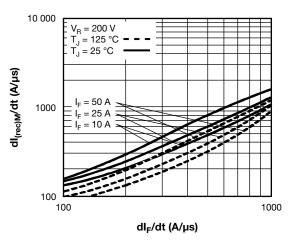


Fig. 8 - Typical  $dI_{(rec)M}/dt$  vs.  $dI_F/dt$ 

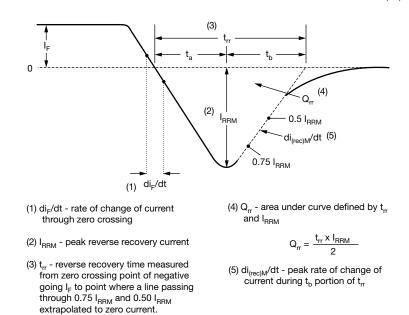


Fig. 9 - Reverse Recovery Waveform and Definitions

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# I<sub>rr</sub> (A)

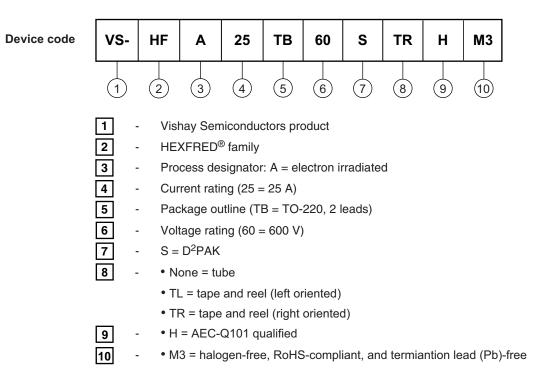
## VS-HFA25TB60SHM3

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**ORDERING INFORMATION TABLE** 

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LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95046					
Part marking information	www.vishay.com/doc?95444					
Packaging information	www.vishay.com/doc?95032					

ORDERING INFORMATION (Example)									
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION							
VS-HFA25TB60SHM3	50	Antistatic plastic tube							
VS-HFA25TB60STRHM3	800	13" diameter reel							
VS-HFA25TB60STLHM3	800	13" diameter reel							

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## **Outline Dimensions**



D<sup>2</sup>PAK

### **DIMENSIONS** in millimeters and inches

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SHA



SYMBOL	MILLIMETERS		INC	HES	NOTES	NOTES	SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STWDUL	MIN.	MAX.	MIN.	MAX.	NOTES
A	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

#### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5 M-1994

<sup>(2)</sup> Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

<sup>(3)</sup> Thermal pad contour optional within dimension E, L1, D1 and E1

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only

<sup>(5)</sup> Datum A and B to be determined at datum plane H

<sup>(6)</sup> Controlling dimension: inch

<sup>(7)</sup> Outline conforms to JEDEC<sup>®</sup> outline TO-263AB

Revision: 08-Jul-15

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